



N-Channel Enhancement Mode Power MOSFET MTN2N60J3

BV_{DSS} : 600V
R_{DS(ON)} : 4.0 Ω (typ.)
I_D : 2A

Description

The MTN2N60J3 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-252 package is universally preferred for all commercial-industrial applications

Features

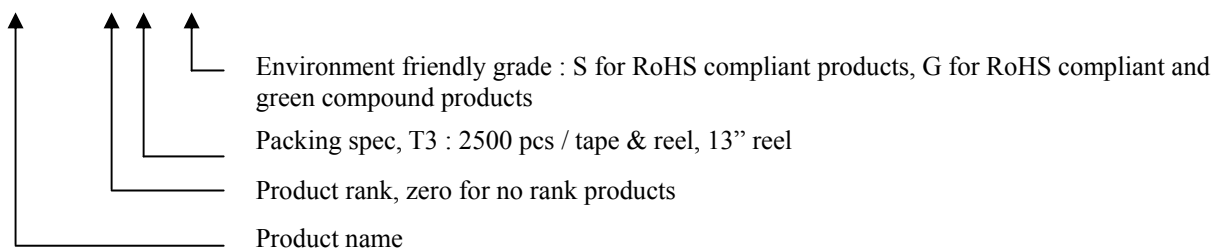
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

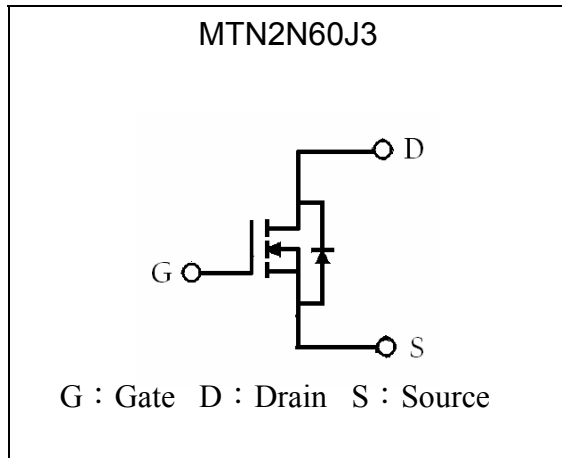
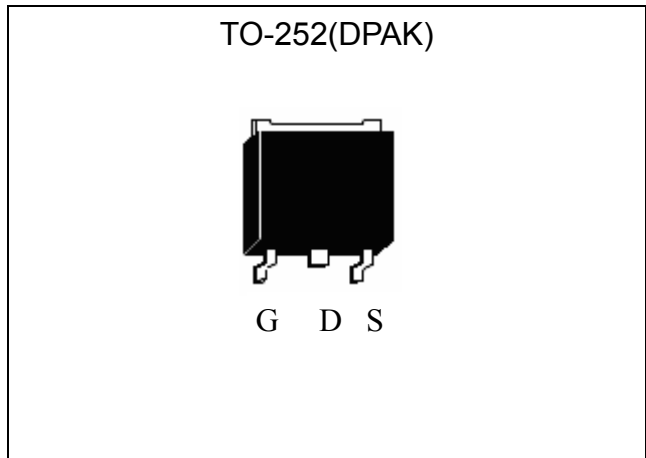
Applications

- Open Framed Power Supply
- Adapter
- STB

Ordering Information

Device	Package	Shipping
MTN2N60J3 -0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Symbol

Outline

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current @ $V_{GS}=10\text{V}$, $T_C=25^\circ\text{C}$	I_D	2	A
Continuous Drain Current @ $V_{GS}=10\text{V}$, $T_C=100^\circ\text{C}$	I_D	1.2	A
Pulsed Drain Current @ $V_{GS}=10\text{V}$ (Note 1)	I_{DM}	8	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	63	mJ
Avalanche Current (Note 1)	I_{AR}	1.9	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	4.4	mJ
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5	V/ns
Maximum Temperature for Soldering @ Lead at 0.125 in(0.318mm) from case for 10 seconds	T_L	300	$^\circ\text{C}$
Total Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	1.14	W
Total Power Dissipation ($T_C=25^\circ\text{C}$)		44	W
Linear Derating Factor		0.35	W/ $^\circ\text{C}$
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+150	$^\circ\text{C}$

Note : 1.Repetitive rating; pulse width limited by maximum junction temperature.

2. $I_{AS}=2\text{A}$, $V_{DD}=50\text{V}$, $L=30\text{mH}$, $R_G=25\Omega$, starting $T_J=+25^\circ\text{C}$.

3. $I_{SD}\leq 2\text{A}$, $dI/dt\leq 100\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, starting $T_J=+25^\circ\text{C}$.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	2.87	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	50 (Note)	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	110	$^\circ\text{C}/\text{W}$

Note : When mounted on the minimum pad size recommended (PCB mount).



Characteristics (Tc=25°C, unless otherwise specified)

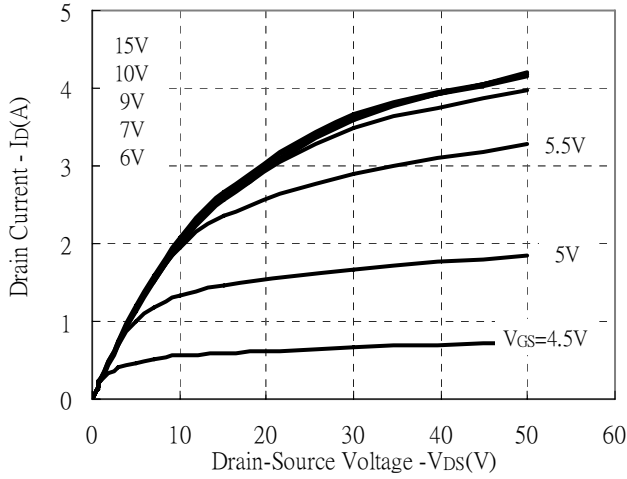
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	600	-	-	V	V _{GS} =0, I _D =250μA, T _j =25°C
ΔBV _{DSS} /ΔT _j	-	0.6	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	1.7	-	S	V _{DS} =15V, I _D =1A
I _{GSS}	-	-	±100	nA	V _{GS} =±30
I _{DSS}	-	-	1	μA	V _{DS} =600V, V _{GS} =0
	-	-	10	μA	V _{DS} =480V, V _{GS} =0, T _C =125°C
*R _{DS(ON)}	-	4	4.7	Ω	V _{GS} =10V, I _D =1A
Dynamic					
*Q _g	-	8.5	-	nC	I _D =2A, V _{DD} =480V, V _{GS} =10V
*Q _{gs}	-	1.3	-		
*Q _{gd}	-	4.1	-		
*t _{d(ON)}	-	9	-	ns	V _{DD} =300V, I _D =2A, V _{GS} =10V, R _G =25 Ω, R _D =150 Ω
*t _r	-	25	-		
*t _{d(OFF)}	-	24	-		
*t _f	-	28	-		
C _{iss}	-	340	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	35	-		
C _{rss}	-	5.2	-		
Source-Drain Diode					
*V _{SD}	-	-	1.4	V	I _S =2A, V _{GS} =0V
*I _S	-	-	2	A	
*I _{SM}	-	-	8		
*t _{rr}	-	230	-	ns	V _{GS} =0, I _F =2A, dI/dt=100A/μs
*Q _{rr}	-	1	-	μC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

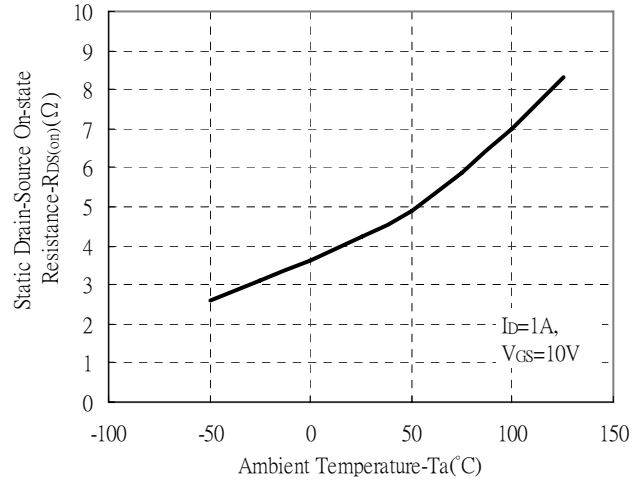


Typical Characteristics

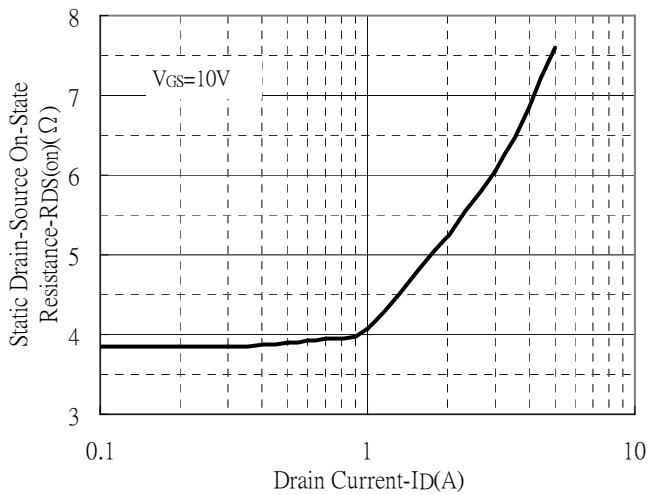
Typical Output Characteristics



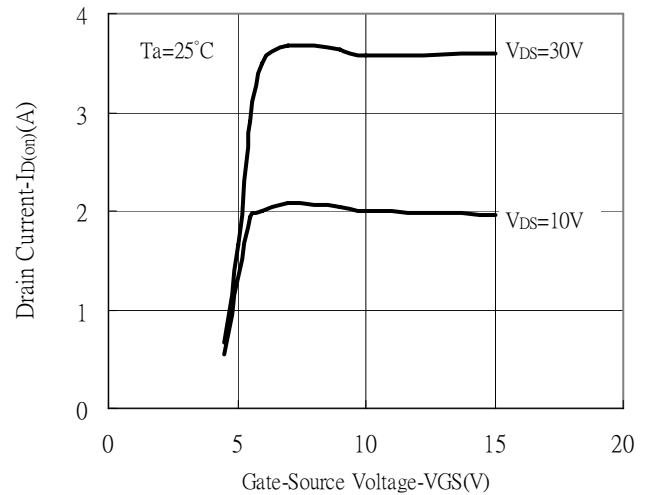
Static Drain-Source On-resistance vs Ambient Temperature



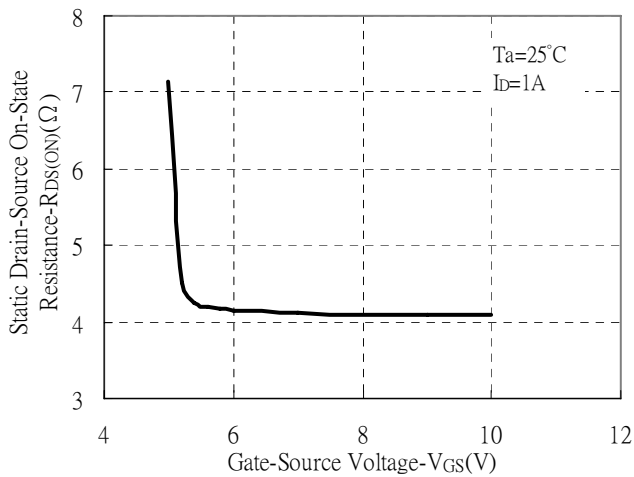
Static Drain-Source On-State resistance vs Drain Current



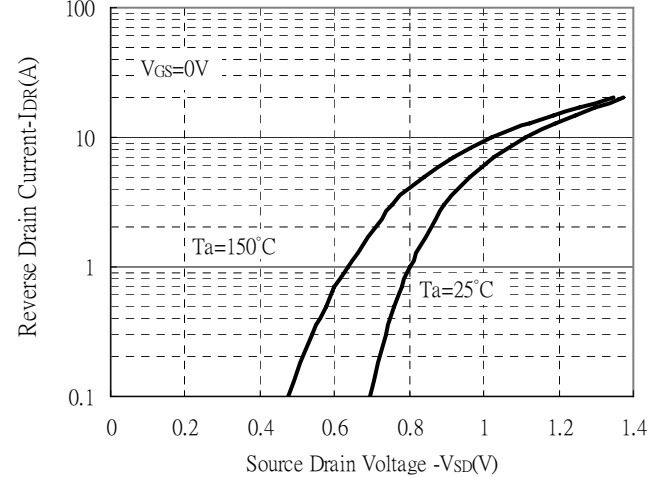
Drain Current vs Gate-Source Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage



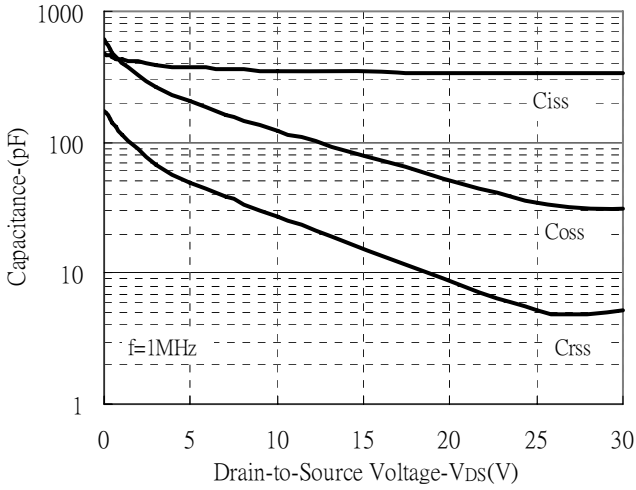
Body Diode Forward Voltage Variation vs Source Current and Temperature



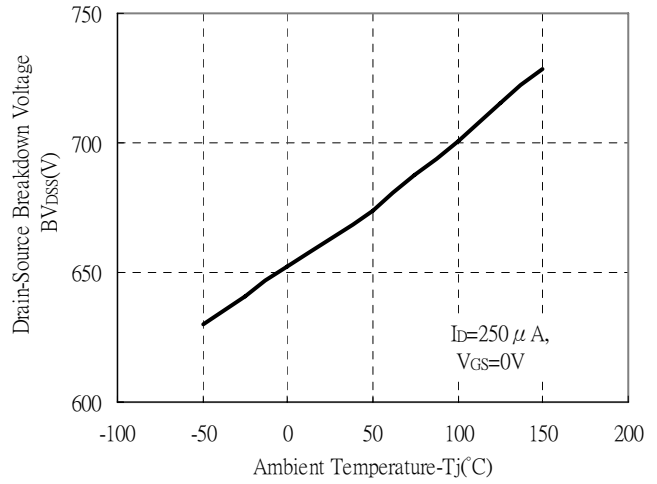


Typical Characteristics(Cont.)

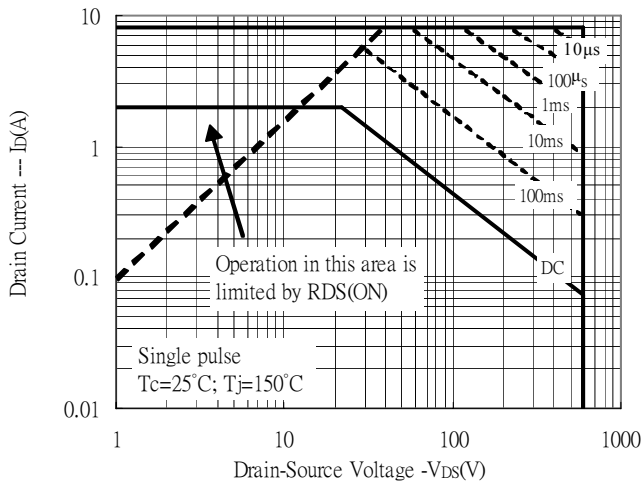
Capacitance vs Reverse Voltage



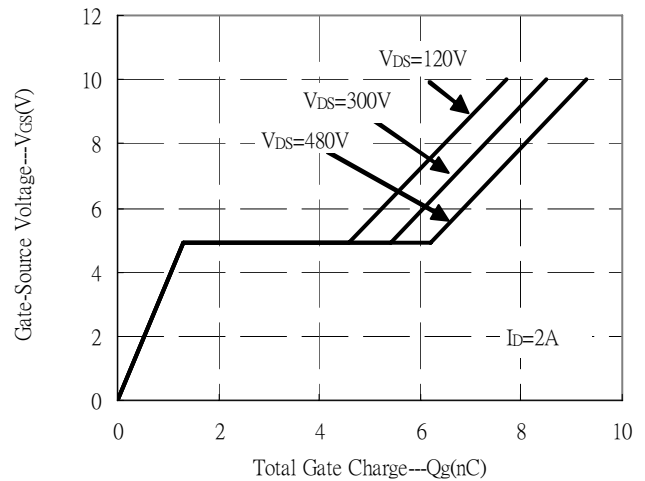
Brekdown Voltage vs Ambient Temperature



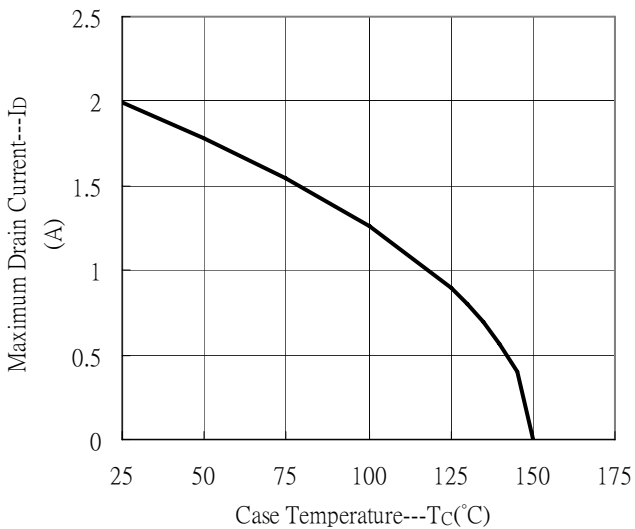
Maximum Safe Operating Area



Gate Charge Characteristics

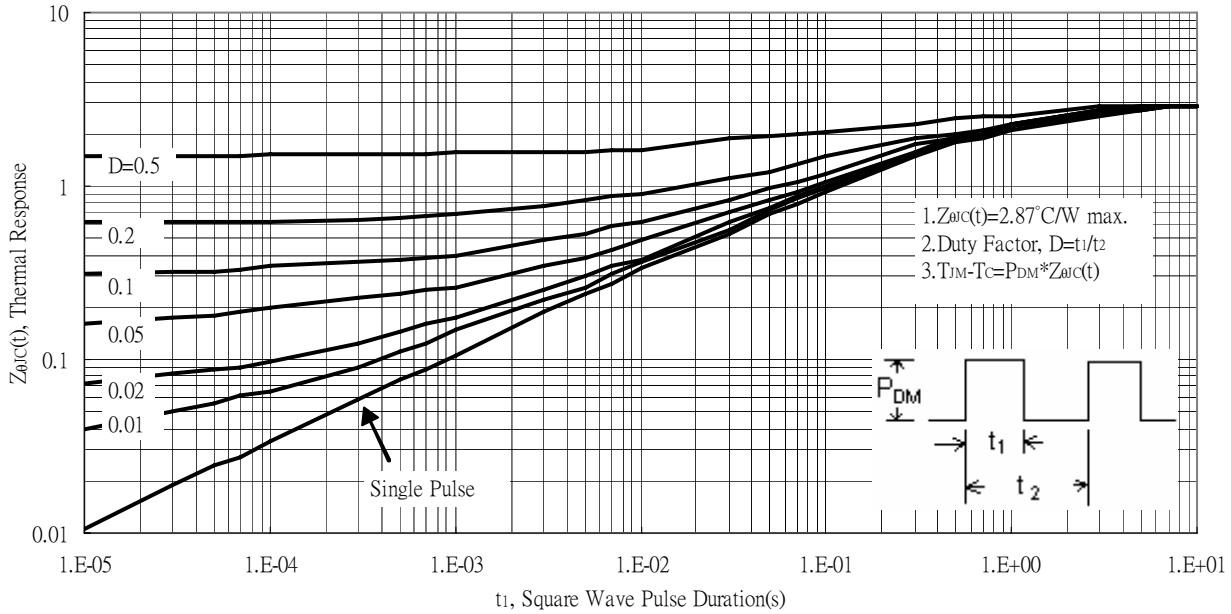


Maximum Drain Current vs Case Temperature

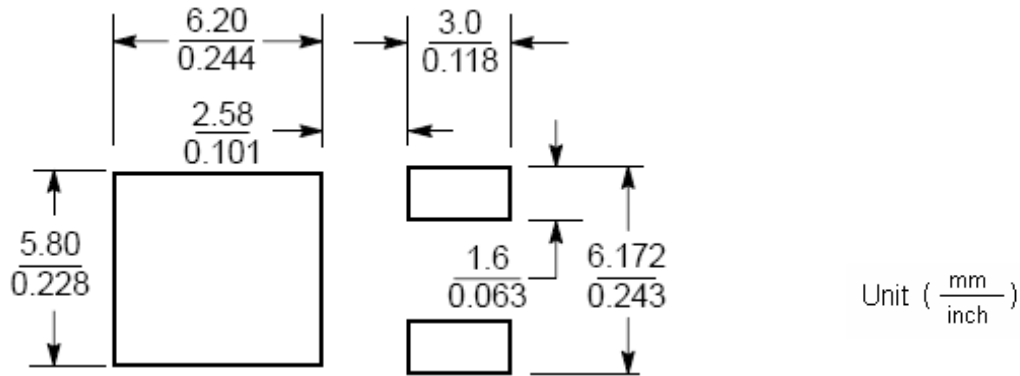


Typical Characteristics(Cont.)

Transient Thermal Response Curves

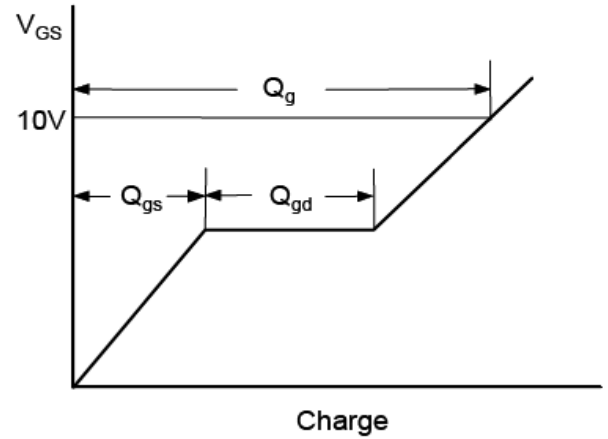
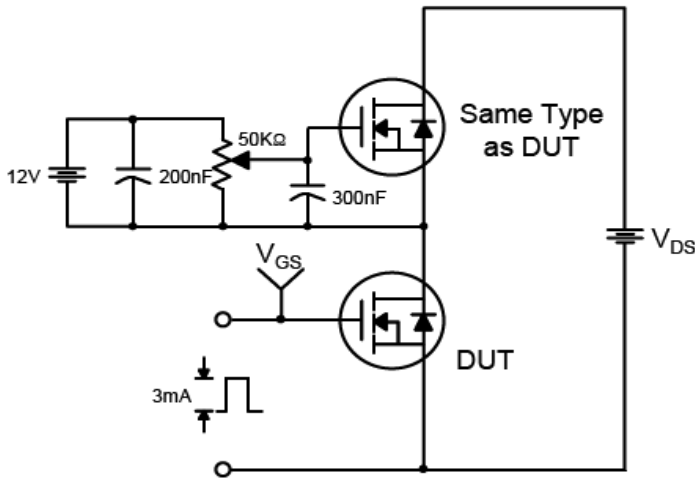


Recommended soldering footprint

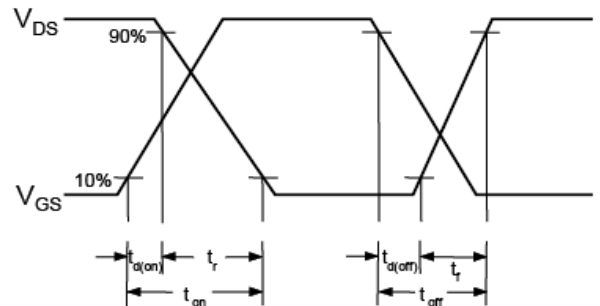
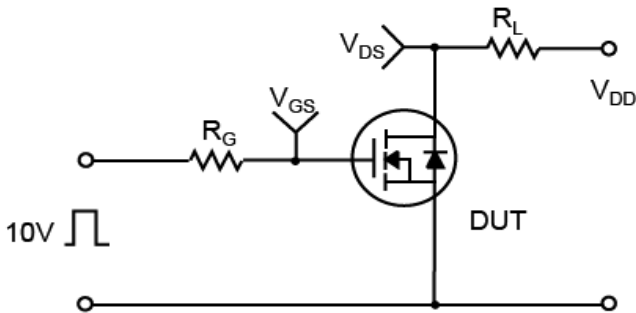


Test Circuits and Waveforms

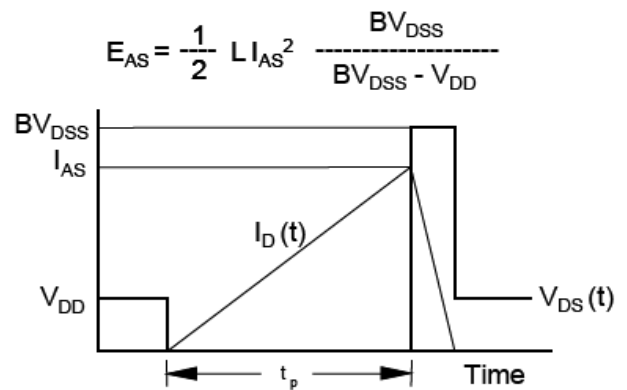
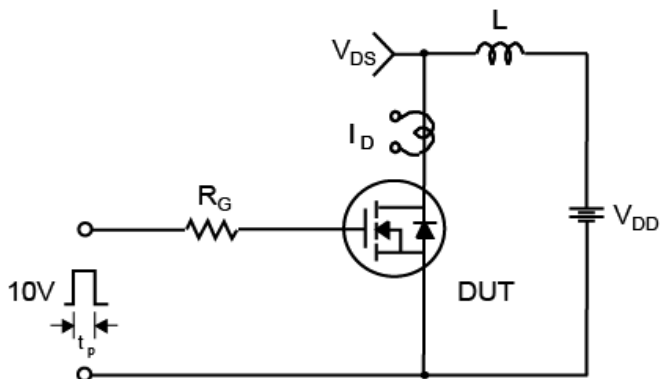
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

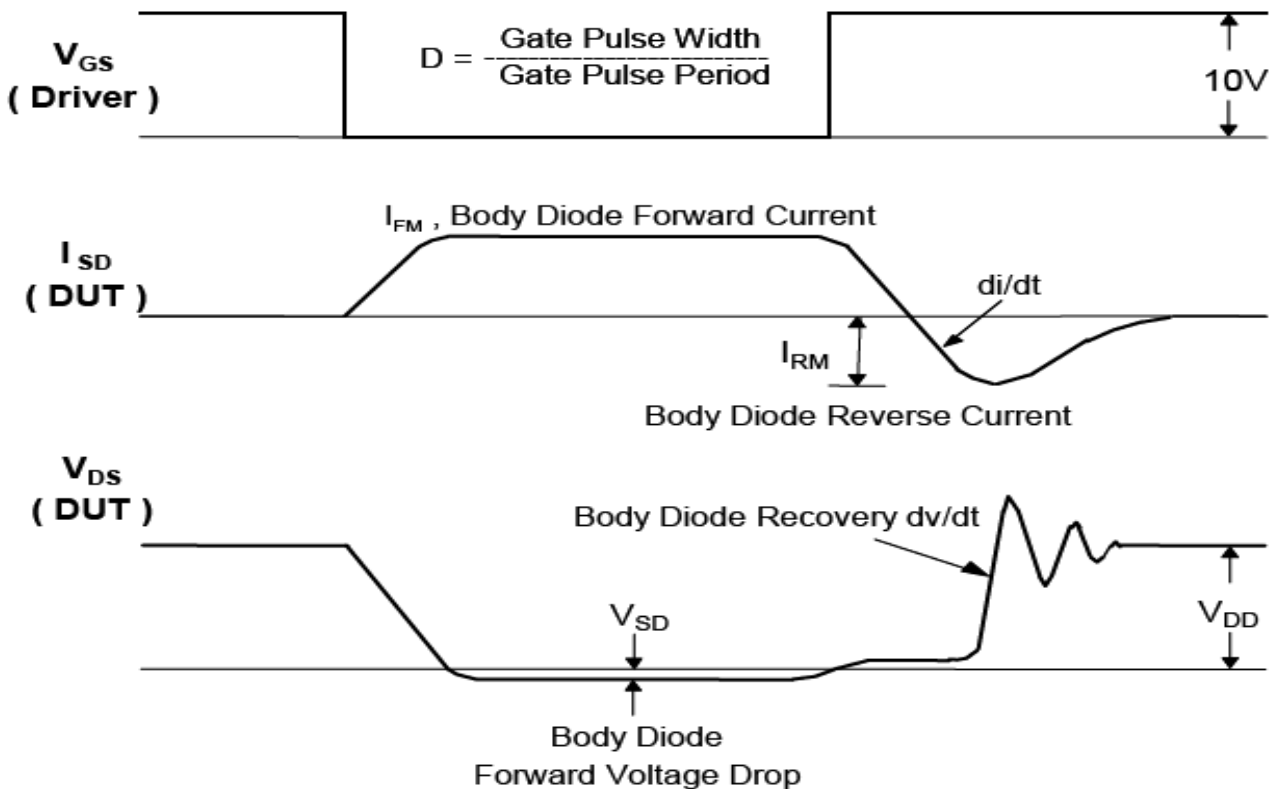
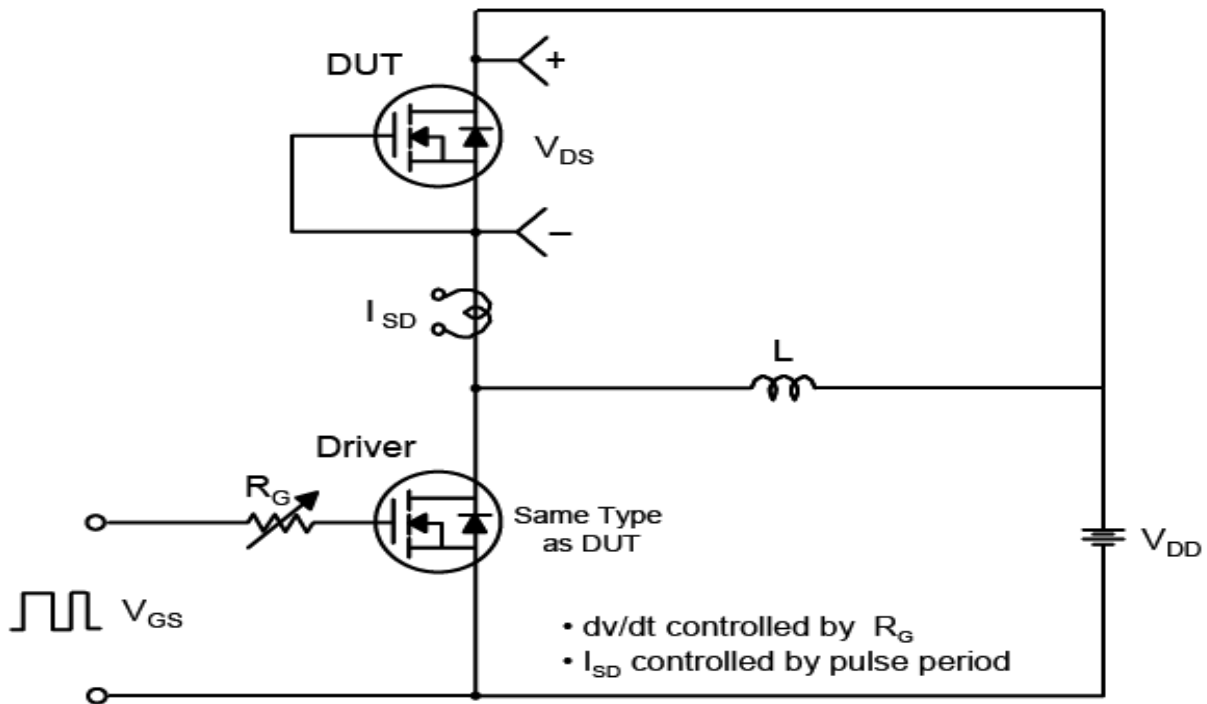


Unclamped Inductive Switching Test Circuit & Waveforms

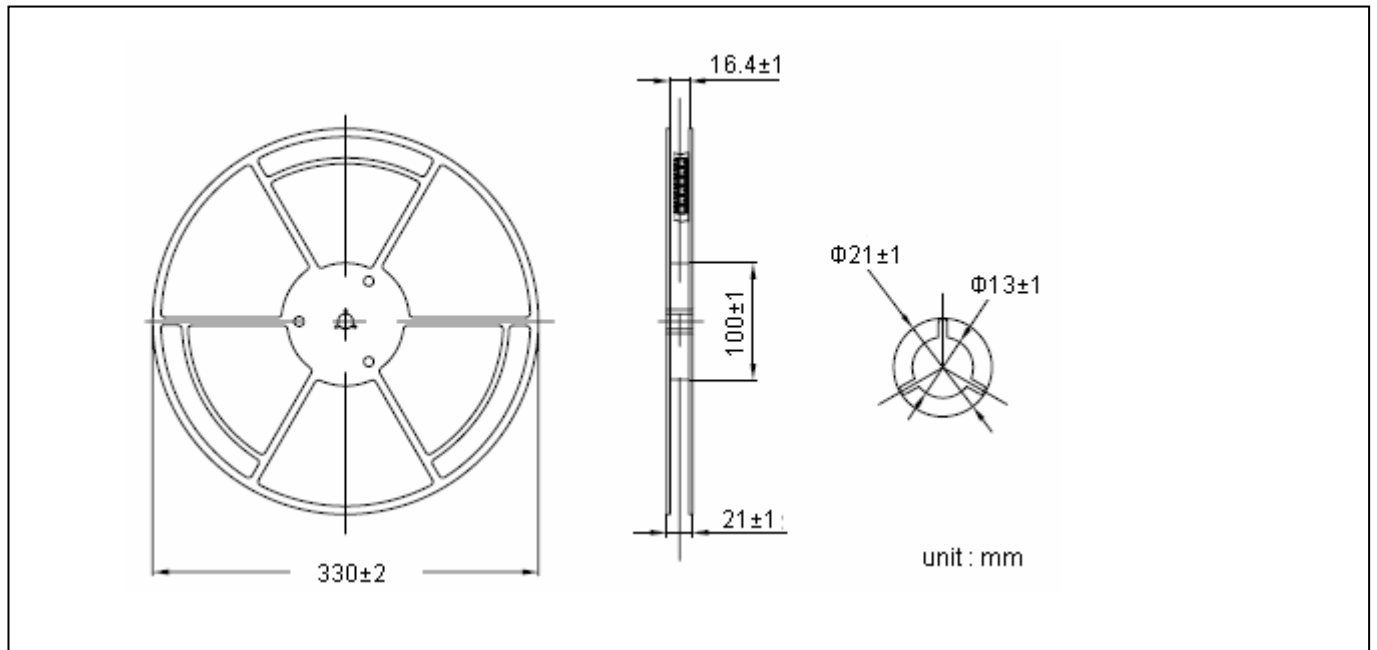


Test Circuits and Waveforms(Cont.)

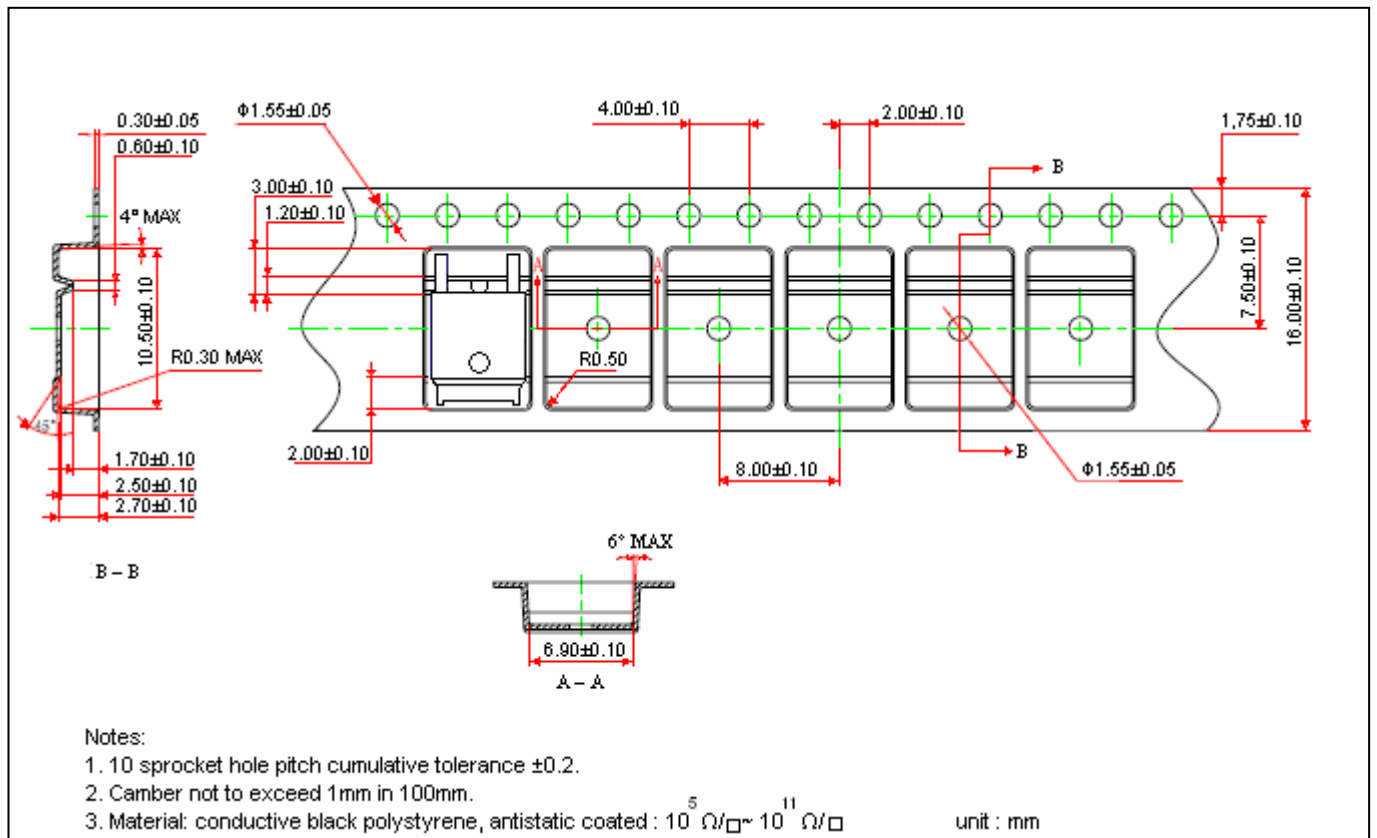
Peak Diode Recovery dv/dt Test Circuit & Waveforms



Reel Dimension



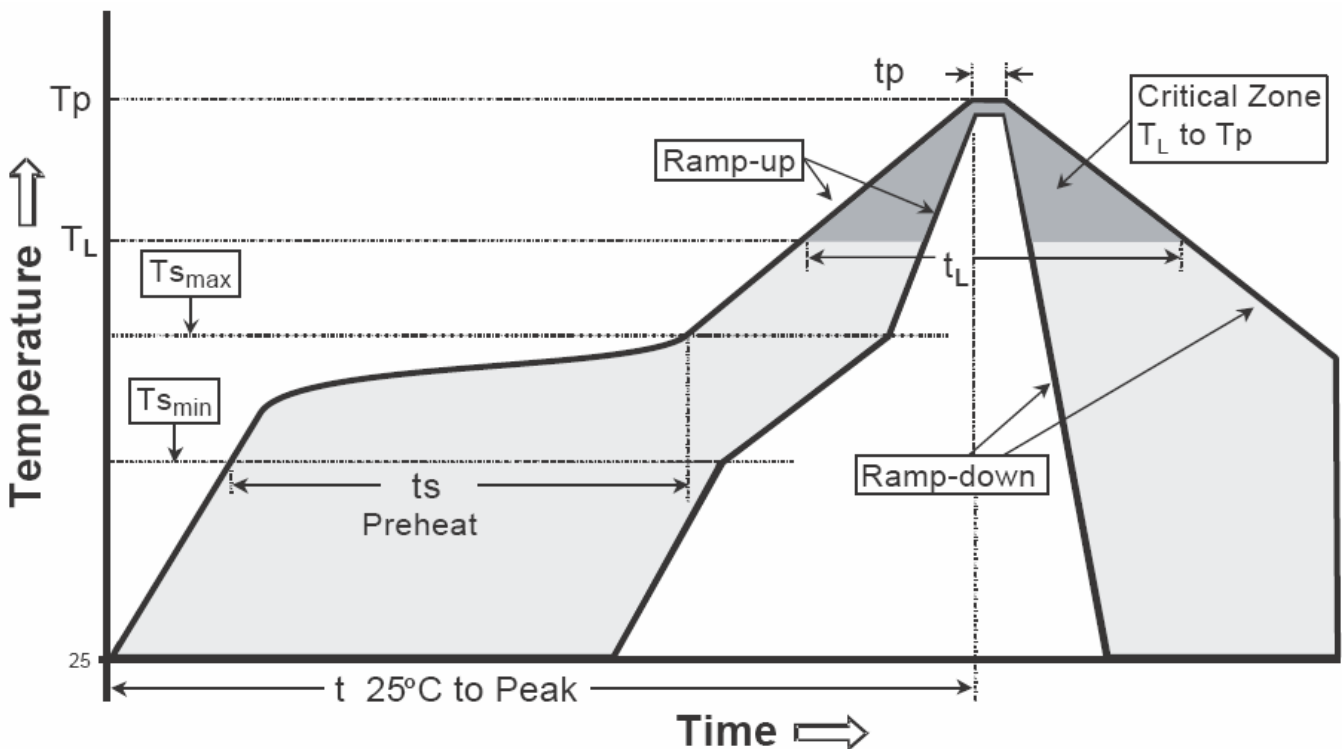
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

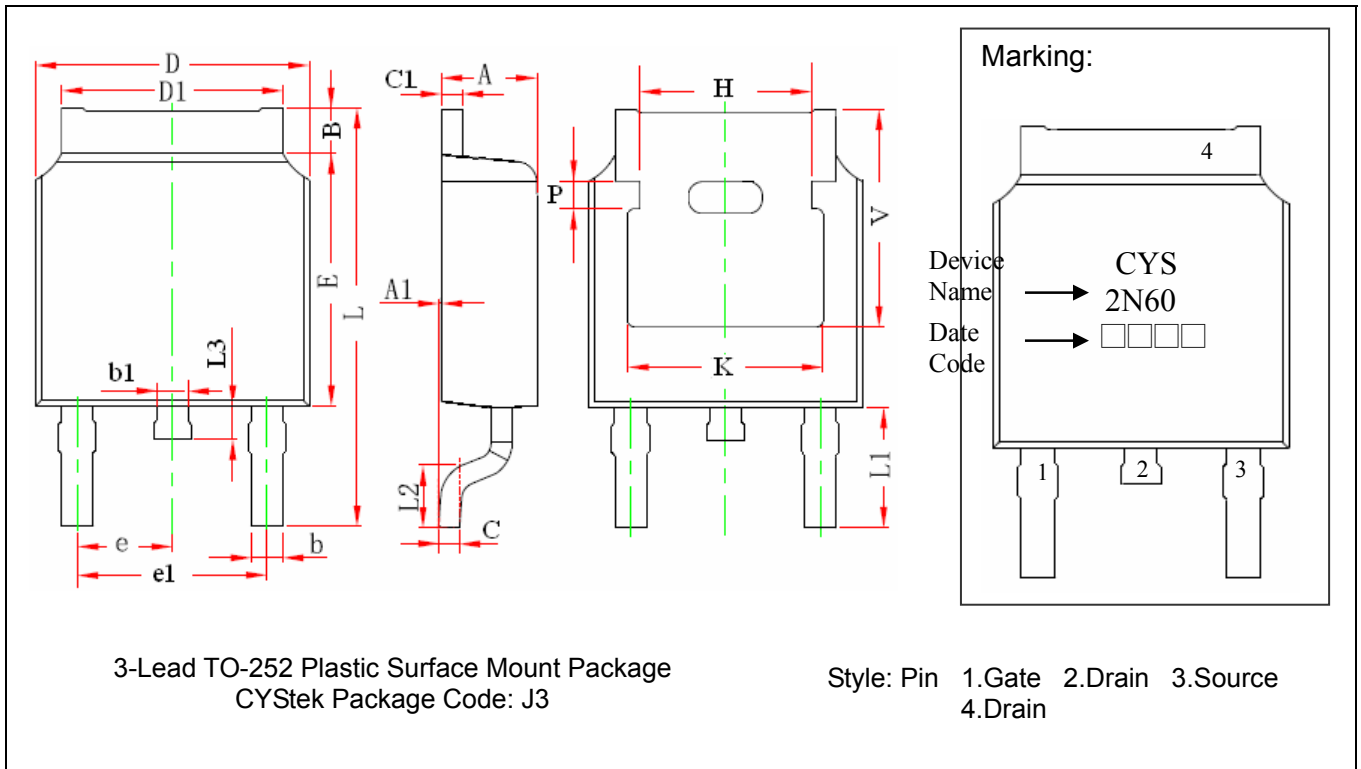
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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